

# TPM4-156.75 4BB

## MONOCSTALLINE SILICON SOLAR CELL

High-efficiency Mono Cells using passivated backside and local BSF Technology. Manufacturing modules with more than **275Wp (6×10)** and **330Wp (6×12)** power output becomes easier than ever.

### MECHANICAL DATA AND DESIGN

Format	156.75mm×156.75mm±0.5mm
Thickness	210µm±30µm
Front(-)	1.1mm bus bars(silver), blue anti-reflecting coating(silicon nitride)
Back(+)	1.6 mm wide soldering pads(silver) back surface field(aluminum)

### TEMPERATURE COEFFICIENTS

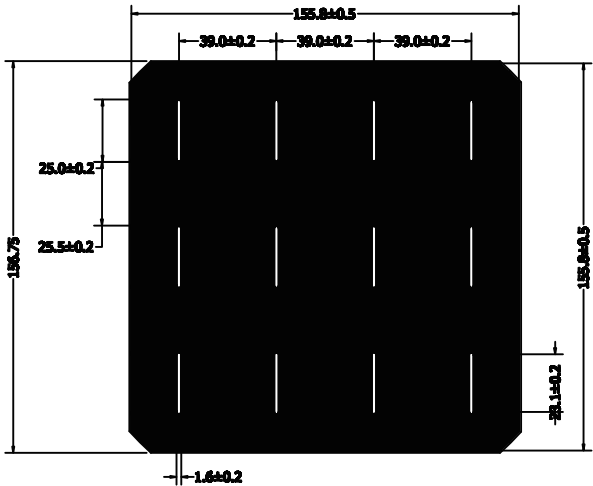
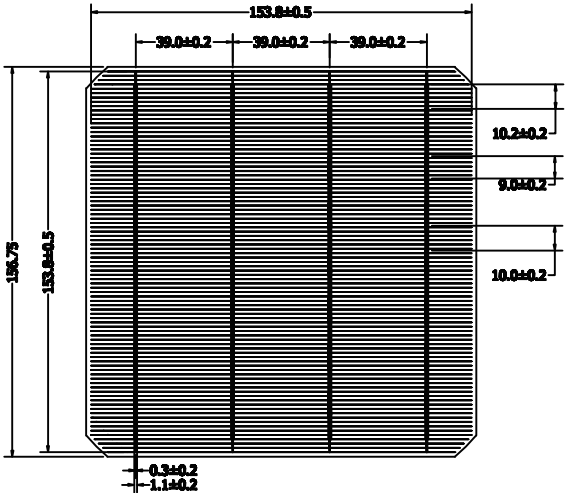
TkVoltage	-0.36%/K
TkCurrent	+0.06%/K
TkPower	-0.36%/K

No.	Efficiency(%)	Pmpp(W)	Umpp(V)	Impp(A)	Uoc(V)	Isc(A)	FF(%)
10	19.80-19.90	4.84	0.543	8.909	0.647	9.424	79.38
09	19.70-19.80	4.81	0.542	8.877	0.645	9.405	79.29
08	19.60-19.70	4.79	0.541	8.855	0.645	9.383	79.14
07	19.50-19.60	4.76	0.540	8.821	0.644	9.365	78.92
06	19.40-19.50	4.74	0.538	8.815	0.643	9.346	78.88
05	19.30-19.40	4.72	0.536	8.798	0.642	9.332	78.78
04	19.20-19.30	4.69	0.535	8.761	0.641	9.313	78.56
03	19.10-19.20	4.67	0.534	8.743	0.640	9.302	78.44
02	19.00-19.10	4.64	0.533	8.708	0.638	9.285	78.33
01	18.90-19.00	4.62	0.532	8.678	0.637	9.267	78.26

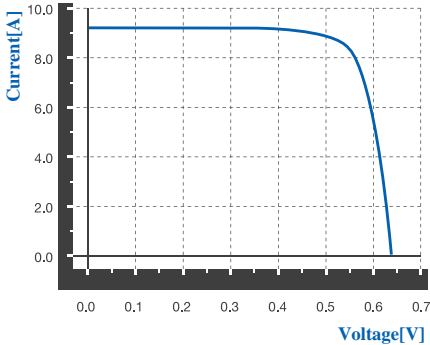
Specifications subjects to technical changes and tests, Taipo Energy reserves the right of final interpretation.

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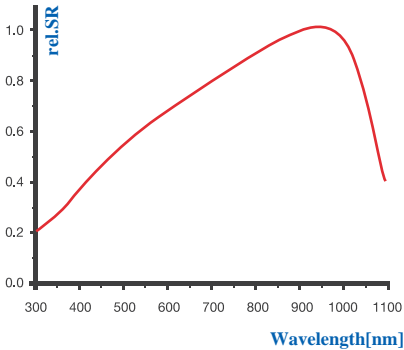
## MONOCRYSTALLINE SILICON SOLAR CELL



**IV CURVE**



**SPECTRAL RESPONSE**



**INTENSITY DEPENDENCE**

Intensity [W/m <sup>2</sup> ]	Isc*	Voc*	Pmpp
1000	1.00	1.00	1.00
900	0.90	1.00	0.90
800	0.80	0.99	0.79
500	0.50	0.97	0.49
300	0.30	0.95	0.29
200	0.20	0.93	0.19

\*Ratio of Voc(Isc) at reduced intensity to Voc(Isc) at 1000 W/m<sup>2</sup>